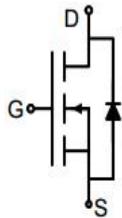
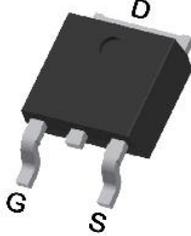


N-Channel Enhancement Mode Power MOSFET

<p>Description</p> <p>The 15N06K uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.</p> <p>General Features</p> <ul style="list-style-type: none"> ● V_{DS} 60V ● I_D (at $V_{GS} = 10V$) 15A ● $R_{DS(ON)}$ (at $V_{GS} = 10V$) < 45mΩ ● $R_{DS(ON)}$ (at $V_{GS} = 4.5V$) < 50mΩ ● 100% Avalanche Tested ● RoHS Compliant <p>Application</p> <ul style="list-style-type: none"> ● Power switch ● DC/DC converters 		 <p>Schematic diagram</p>  <p>TO-252</p>	
Device	Package	Marking	Packaging
15N06K	TO-252	15N06	2500pcs/Reel

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

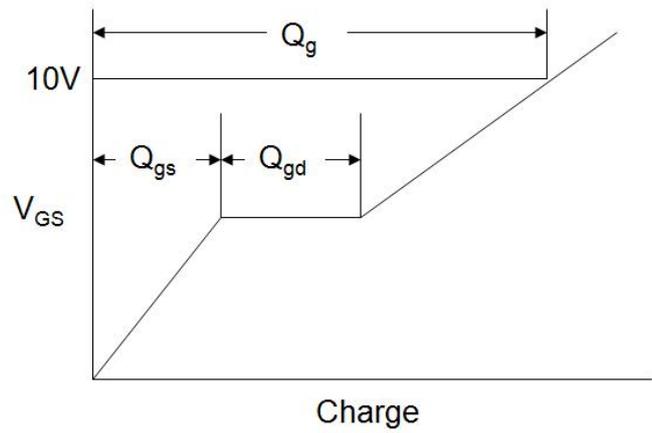
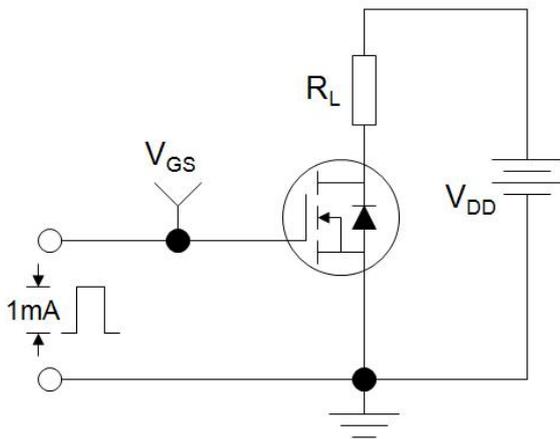
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Continuous Drain Current	I_D	15	A
Pulsed Drain Current (note1)	I_{DM}	60	A
Gate-Source Voltage	V_{GS}	± 20	V
Single Pulse Avalanche Energy (note3)	E_{AS}	12	mJ
Power Dissipation	P_D	40	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	$^\circ\text{C}$

Thermal Resistance

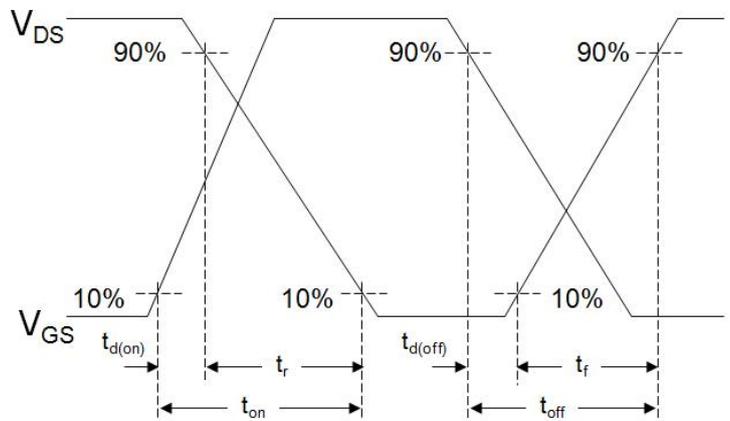
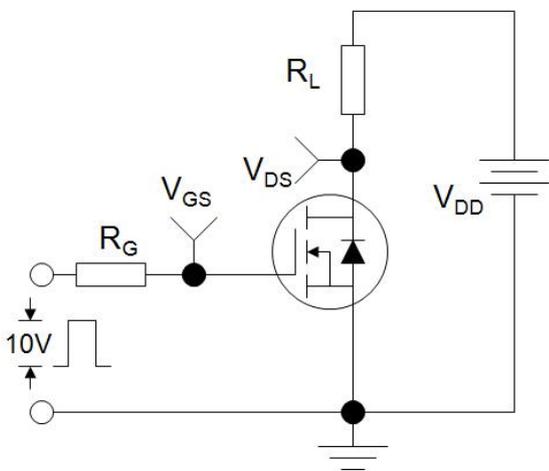
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	3.1	$^\circ\text{C/W}$

Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 100V, V_{GS} = 0V$	--	--	1	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.9	3	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 8A$	--	31	45	m Ω
		$V_{GS} = 4.5V, I_D = 6A$	--	39	50	
Forward Transconductance	g_{FS}	$V_{DS}=25V, I_D=8A$	--	17.4	--	S
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 30V,$ $f = 1.0MHz$	--	763	--	pF
Output Capacitance	C_{oss}		--	41	--	
Reverse Transfer Capacitance	C_{rss}		--	37	--	
Total Gate Charge	Q_g	$V_{DD} = 50V,$ $I_D = 10A,$ $V_{GS} = 10V$	--	25	--	nC
Gate-Source Charge	Q_{gs}		--	4.5	--	
Gate-Drain Charge	Q_{gd}		--	6.5	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 30V,$ $I_D = 10A,$ $R_G = 3\Omega$	--	7	--	ns
Turn-on Rise Time	t_r		--	20	--	
Turn-off Delay Time	$t_{d(off)}$		--	16	--	
Turn-off Fall Time	t_f		--	23	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	15	A
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{SD} = 8A, V_{GS} = 0V$	--	--	1.2	V

Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit

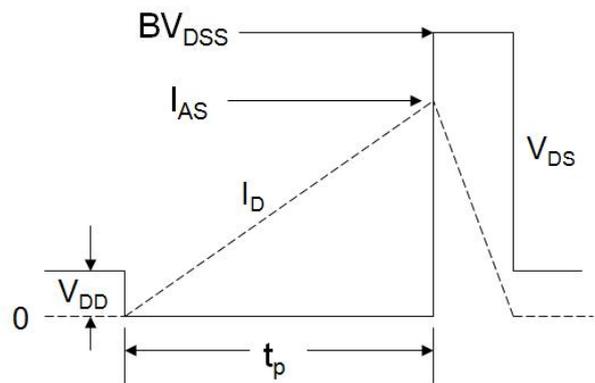
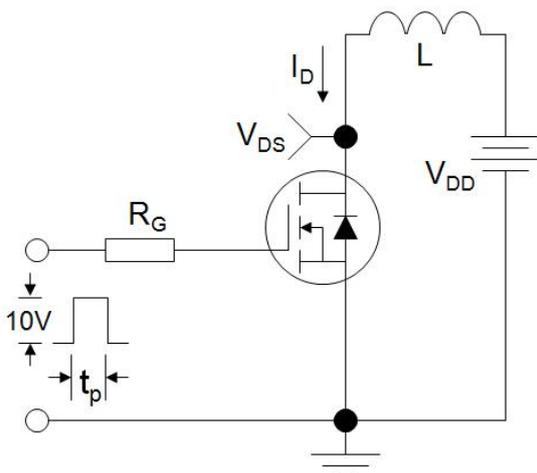


Figure 1. Output Characteristics

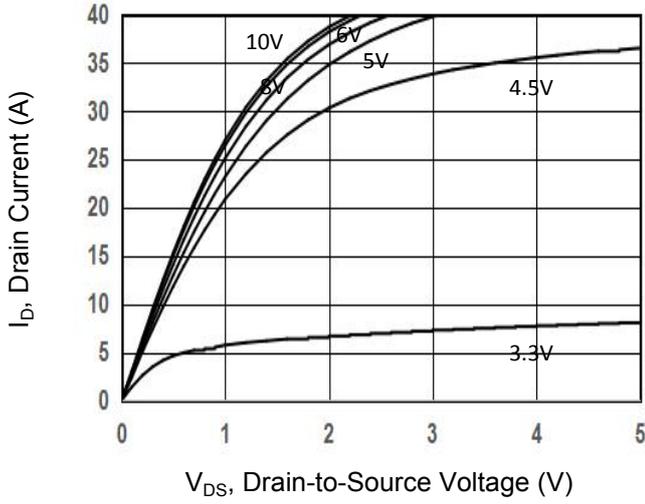


Figure 2. Transfer Characteristics

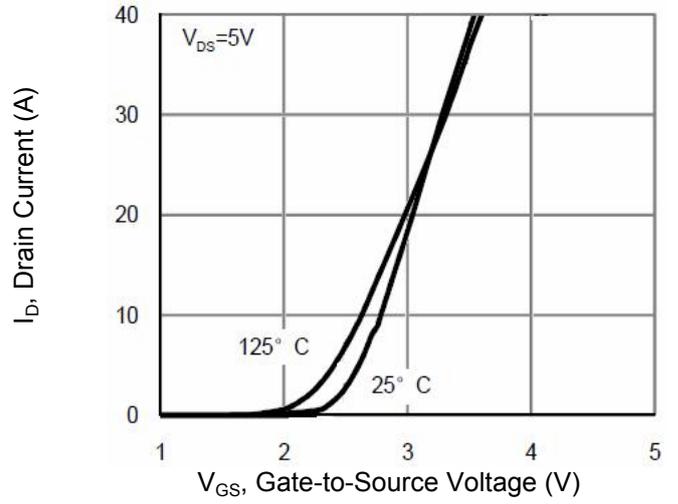


Figure 3. Gate Charge

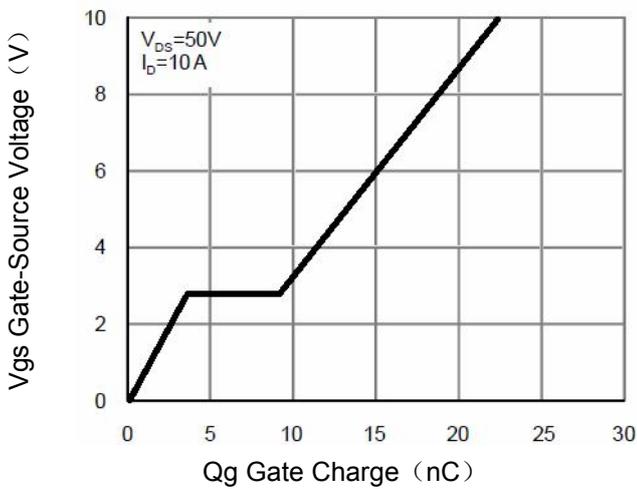


Figure 4. Drain Source On Resistance

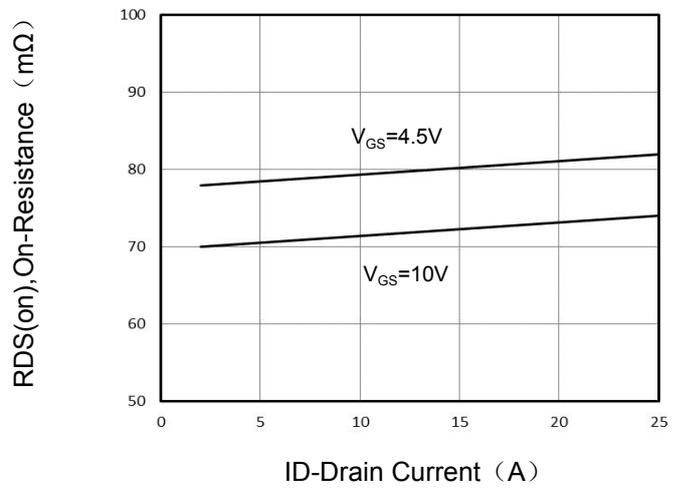


Figure 5. Capacitance

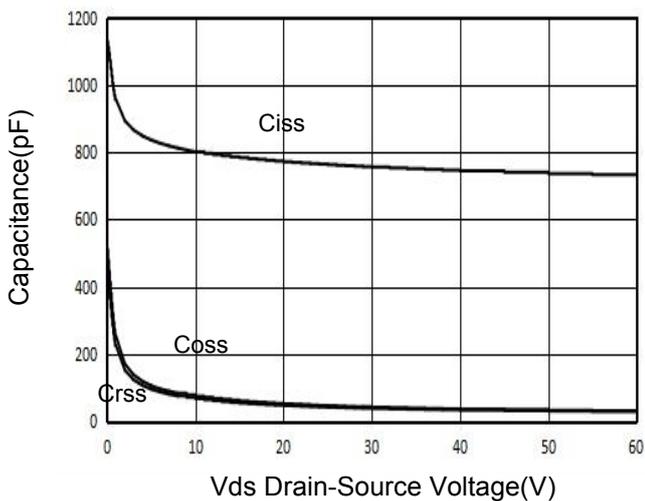
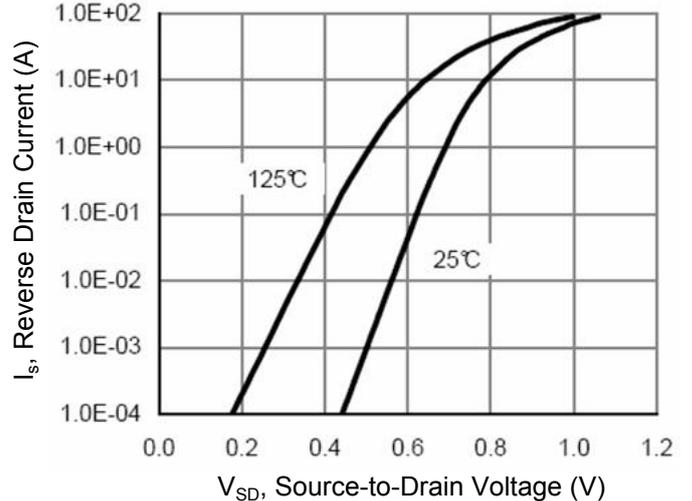


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

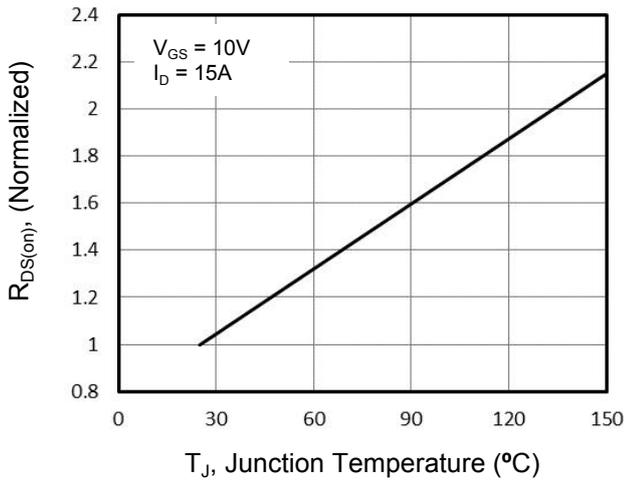


Figure 8. Safe Operation Area

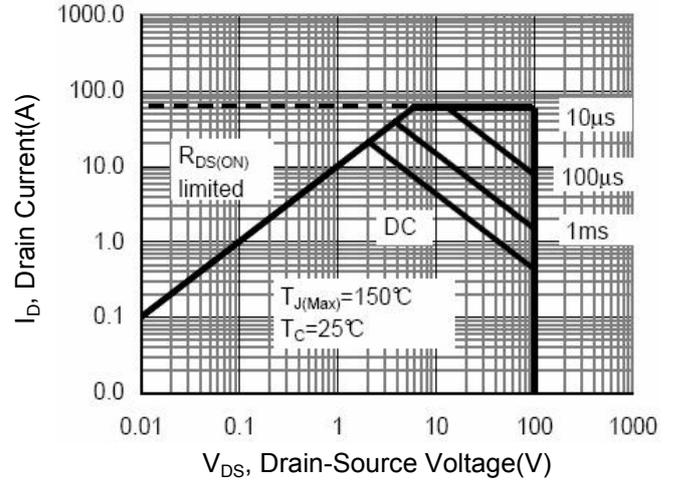
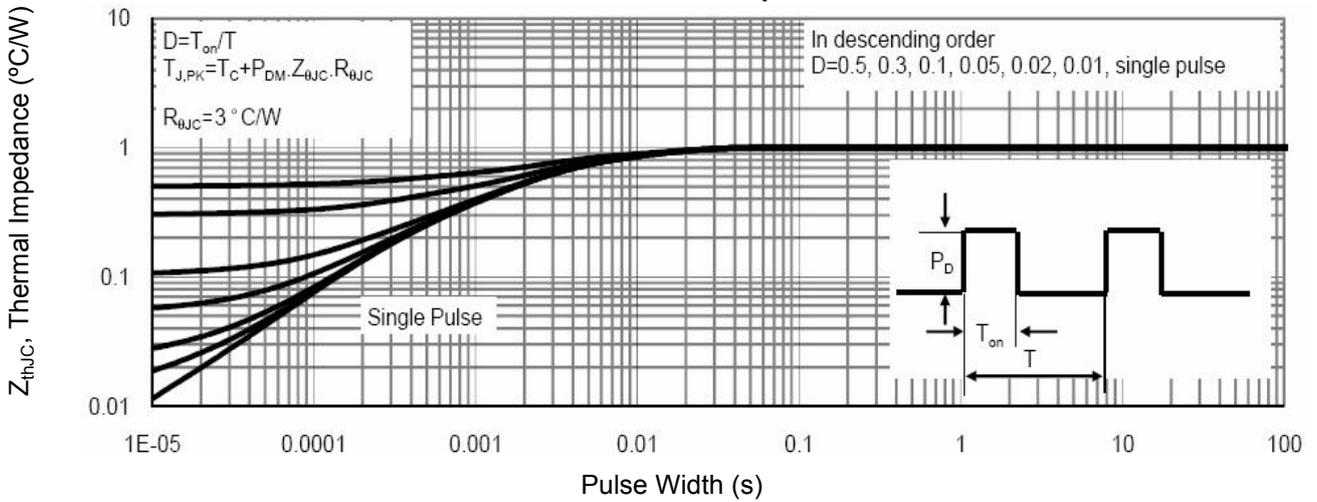
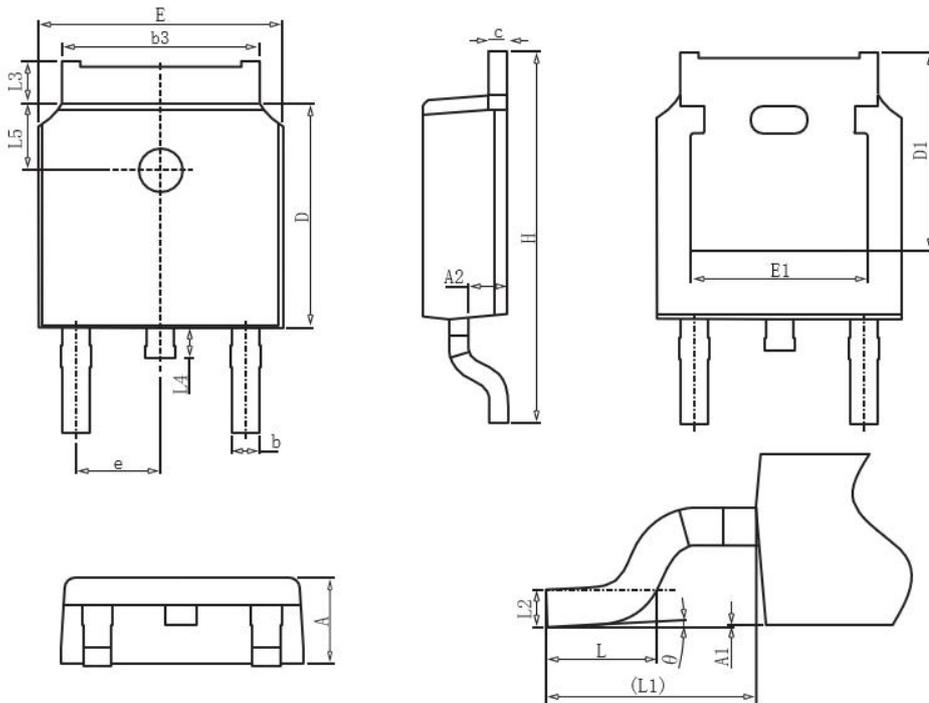


Figure 9. Normalized Maximum Transient Thermal Impedance



TO-252 Package Information



Symbol	Dimensions in Millimeters		
	MIN.	NOM.	MAX.
A	2.2	2.3	2.4
A1	0		0.2
A2	0.97	1.07	1.17
b	0.68	0.78	0.9
b3	5.2	5.33	5.5
c	0.43	0.53	0.63
D	5.98	6.1	6.22
D1	5.30REF		
E	6.4	6.6	6.8
E1	4.63		
e	2.286BSC		
H	9.4	10.1	10.5
L	1.38	1.5	1.75
L1	2.90REF		
L2	0.51BSC		
L3	0.88		1.28
L4	0.5		1
L5	1.65	1.8	1.95
θ	0°		8°